

Silicon Diffused Power Transistor

BU2520DX

GENERAL DESCRIPTION

New generation, high-voltage, high-speed switching npn transistor with an integrated damper diode in a full plastic envelope intended for use in horizontal deflection circuits of large screen colour television receivers.

QUICK REFERENCE DATA

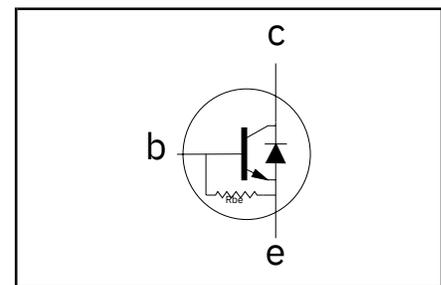
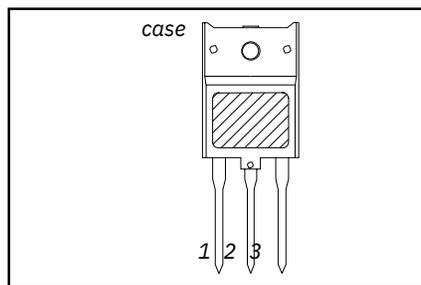
SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
VCESM	Collector-emitter voltage peak value	$V_{BE} = 0 \text{ V}$	-	1500	V
VCEO	Collector-emitter voltage (open base)		-	800	V
IC	Collector current (DC)		-	10	A
ICM	Collector current peak value		-	25	A
Ptot	Total power dissipation	$T_{hs} \leq 25 \text{ }^\circ\text{C}$	-	45	W
VCEsat	Collector-emitter saturation voltage	$I_C = 6.0 \text{ A}; I_B = 1.2 \text{ A}$	-	5.0	V
ICsat	Collector saturation current		6	-	A
VF	Diode forward voltage	$I_F = 6.0 \text{ A}$	-	2.2	V
tf	Fall time	$I_{Csat} = 6.0 \text{ A}; I_{B(end)} = 1.0 \text{ A}$	0.35	0.5	μs

PINNING - SOT399

PIN CONFIGURATION

SYMBOL

PIN	DESCRIPTION
1	base
2	collector
3	emitter
case	isolated



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum Rating System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
VCESM	Collector-emitter voltage peak value	$V_{BE} = 0 \text{ V}$	-	1500	V
VCEO	Collector-emitter voltage (open base)		-	800	V
IC	Collector current (DC)		-	10	A
ICM	Collector current peak value		-	25	A
IB	Base current (DC)		-	6	A
IBM	Base current peak value		-	9	A
-IB(AV)	Reverse base current average over any 20 ms period		-	150	mA
-IR	Reverse base current peak value		-	6	A
Ptot	Total power dissipation	$T_{hs} \leq 25 \text{ }^\circ\text{C}$	-	45	W
Tstg	Storage temperature		-55	150	$^\circ\text{C}$
Tj	Junction temperature		-	150	$^\circ\text{C}$

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
Rth j-hs	Junction to heatsink	with heatsink compound	-	2.8	K/W
Rth j-a	Junction to ambient	in free air	35	-	K/W

¹ Turn-off current.

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ISOLATION LIMITING VALUE & CHARACTERISTICT_{hs} = 25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
	Visol	Repetitive peak voltage from all three terminals to external heatsink			2500	V
	Cisol	Capacitance from T2 to external heatsink		22		pF

STATIC CHARACTERISTICST_{hs} = 25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CE}	Collector cut-off current	V _{BE} = 0 V; V _{CE} = V _{CESMmax}	-	-	1.0	mA
I _{CE(sat)}	Collector cut-off current	V _{BE} = 0 V; V _{CE} = V _{CESMmax} ; T _j = 125 °C	-	-	2.0	mA
I _{EO}	Emitter cut-off current	V _{EB} = 7.5 V; I _C = 0 A	100	-	300	mA
V _{BEBO}	Emitter-base breakdown voltage	I _B = 600 mA	7.5	13.5	-	V
r _{be}	Base-emitter resistance	V _{EB} = 7.5 V	-	50	-	Ω
V _{CE(sust)}	Collector-emitter sustaining voltage	I _B = 0 A; I _C = 100 mA; L = 25 mH	800	-	-	V
V _{CE(sat)}	Collector-emitter saturation voltage	I _C = 6.0 A; I _B = 1.2 A	-	-	5.0	V
V _{BE(sat)}	Base-emitter saturation voltage	I _C = 6.0 A; I _B = 1.2 A	-	-	1.1	V
h _{FE}	DC current gain	I _C = 1.0 A; V _{CE} = 5 V	-	13	-	
h _{FE}	DC current gain	I _C = 6 A; V _{CE} = 5 V	5	7	9.5	V
V _F	Diode forward voltage	I _F = 6 A	-	-	2.2	V

DYNAMIC CHARACTERISTICST_{mb} = 25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
C _c	Collector capacitance	I _E = 0 A; V _{CB} = 10 V; f = 1 MHz	115	-	pF
t _s	Turn-off storage time	Switching times (16 kHz line deflection circuit)			
t _f	Turn-off fall time	I _{C(sat)} = 6.0 A; L _C = 650 μH; C _{fb} = 19 nF; I _{B(end)} = 1.0 A; L _B = 5.3 μH; -V _{BB} = 4 V; (-dI _B /dt = 0.8 A / μs)	4.5	5.	μs
			0.3	5	μs

2 Measured with half sine-wave voltage (curve tracer).

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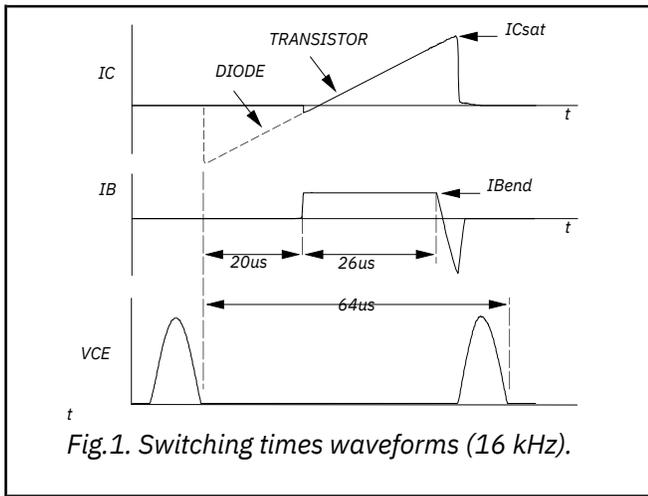


Fig.1. Switching times waveforms (16 kHz).

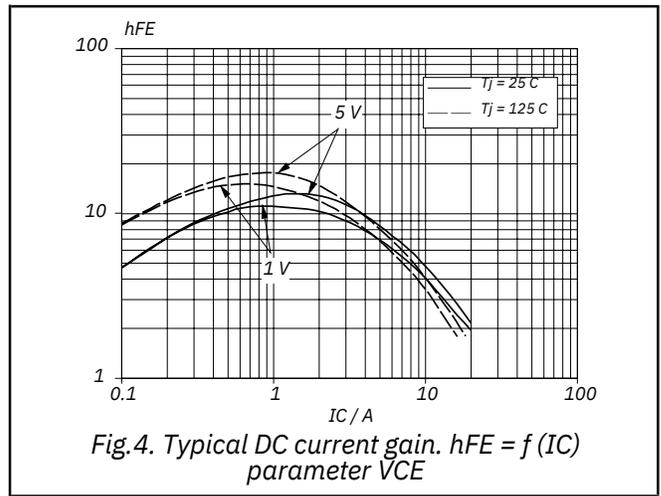


Fig.4. Typical DC current gain, $h_{FE} = f(I_C)$ parameter V_{CE}

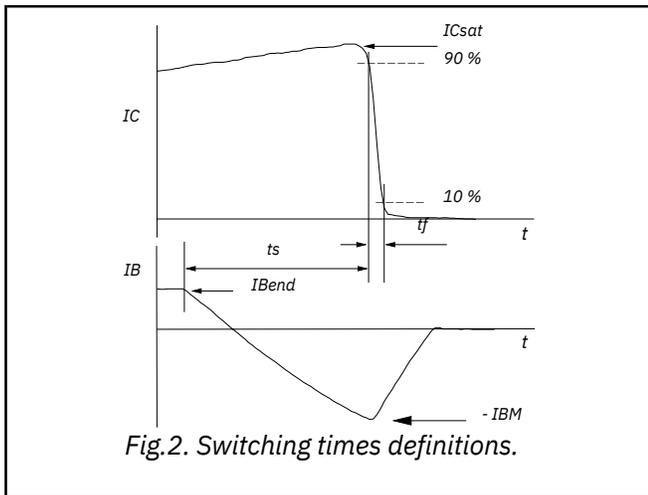


Fig.2. Switching times definitions.

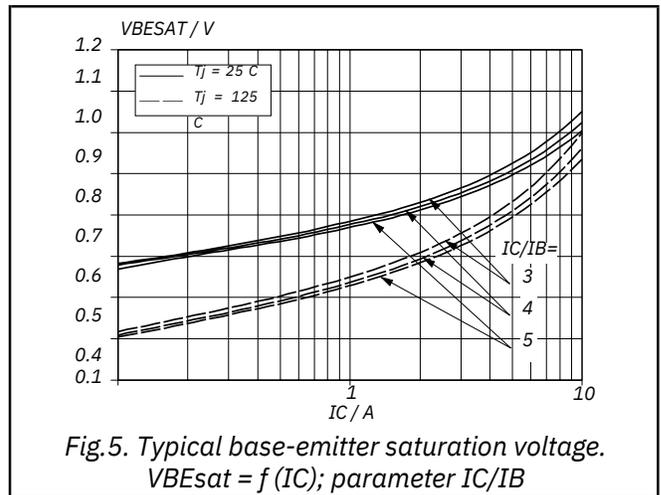


Fig.5. Typical base-emitter saturation voltage, $V_{BEsat} = f(I_C)$; parameter I_C/I_B

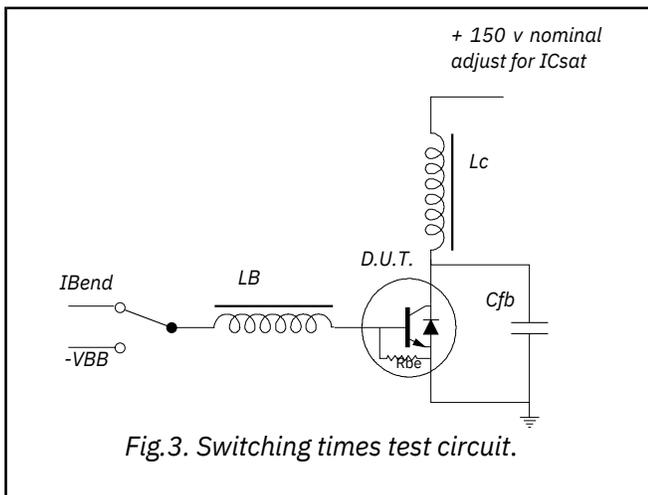


Fig.3. Switching times test circuit.

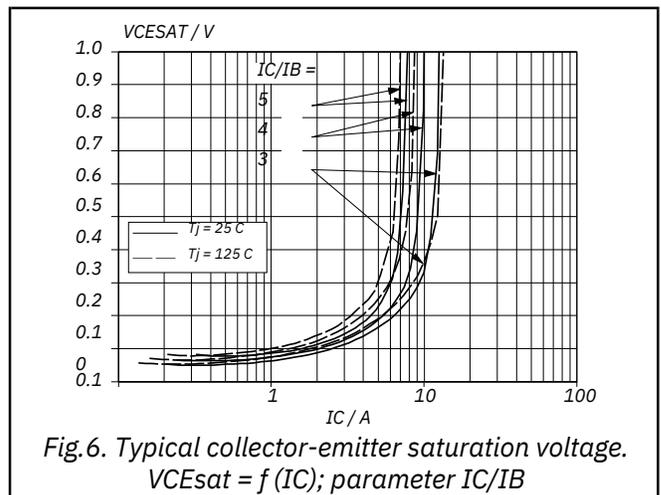
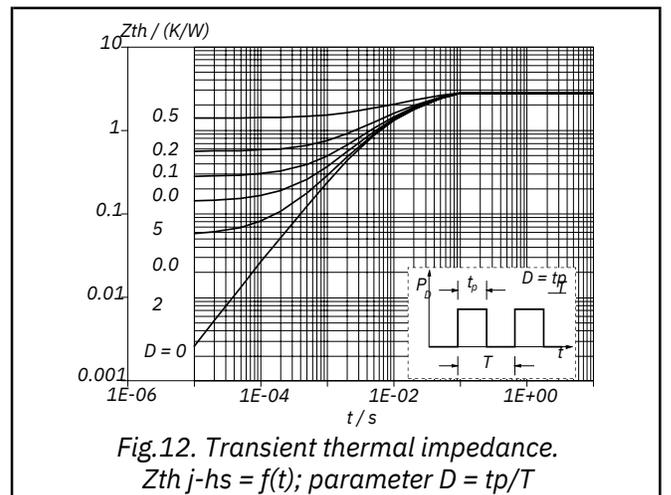
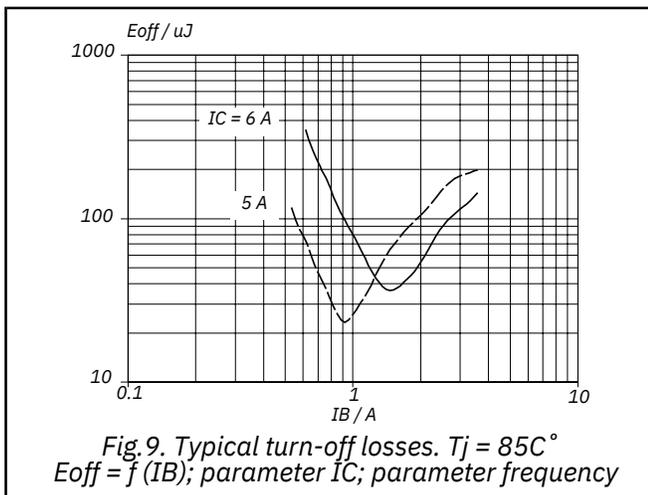
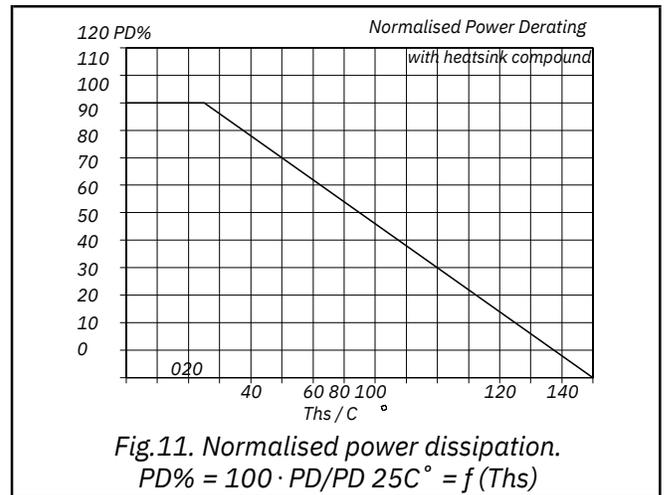
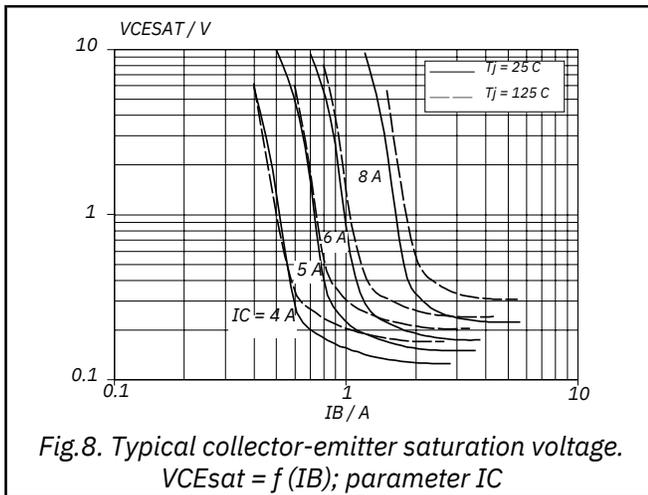
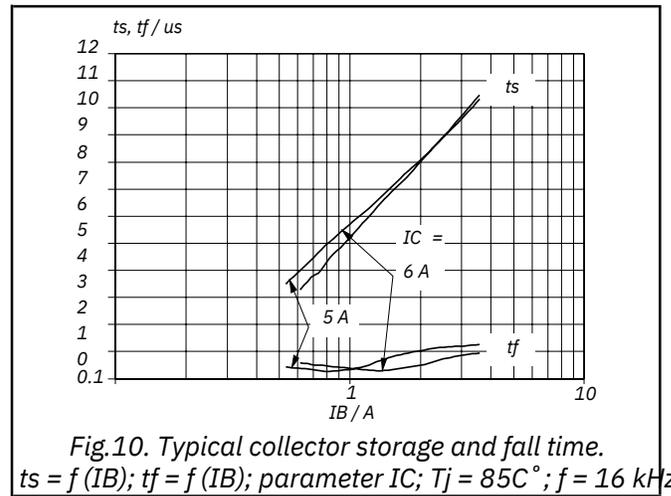
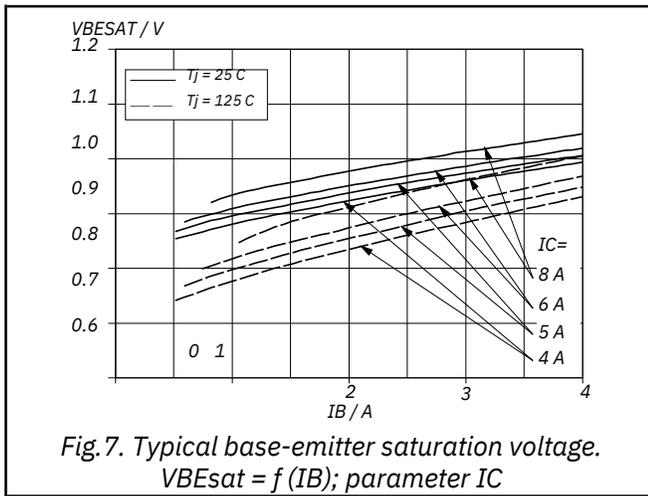


Fig.6. Typical collector-emitter saturation voltage, $V_{CEsat} = f(I_C)$; parameter I_C/I_B

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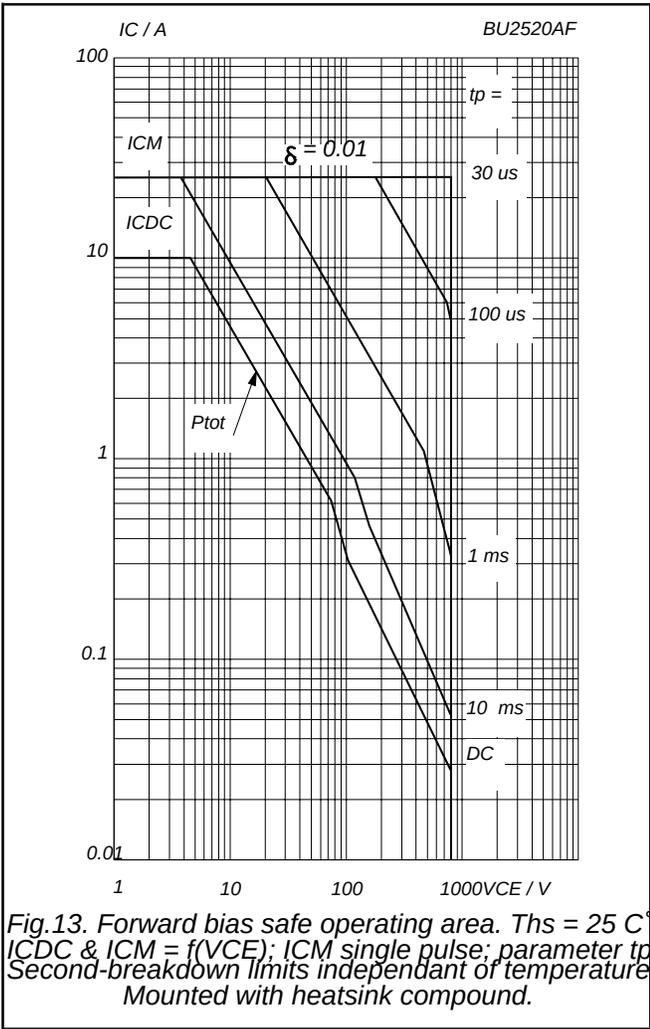
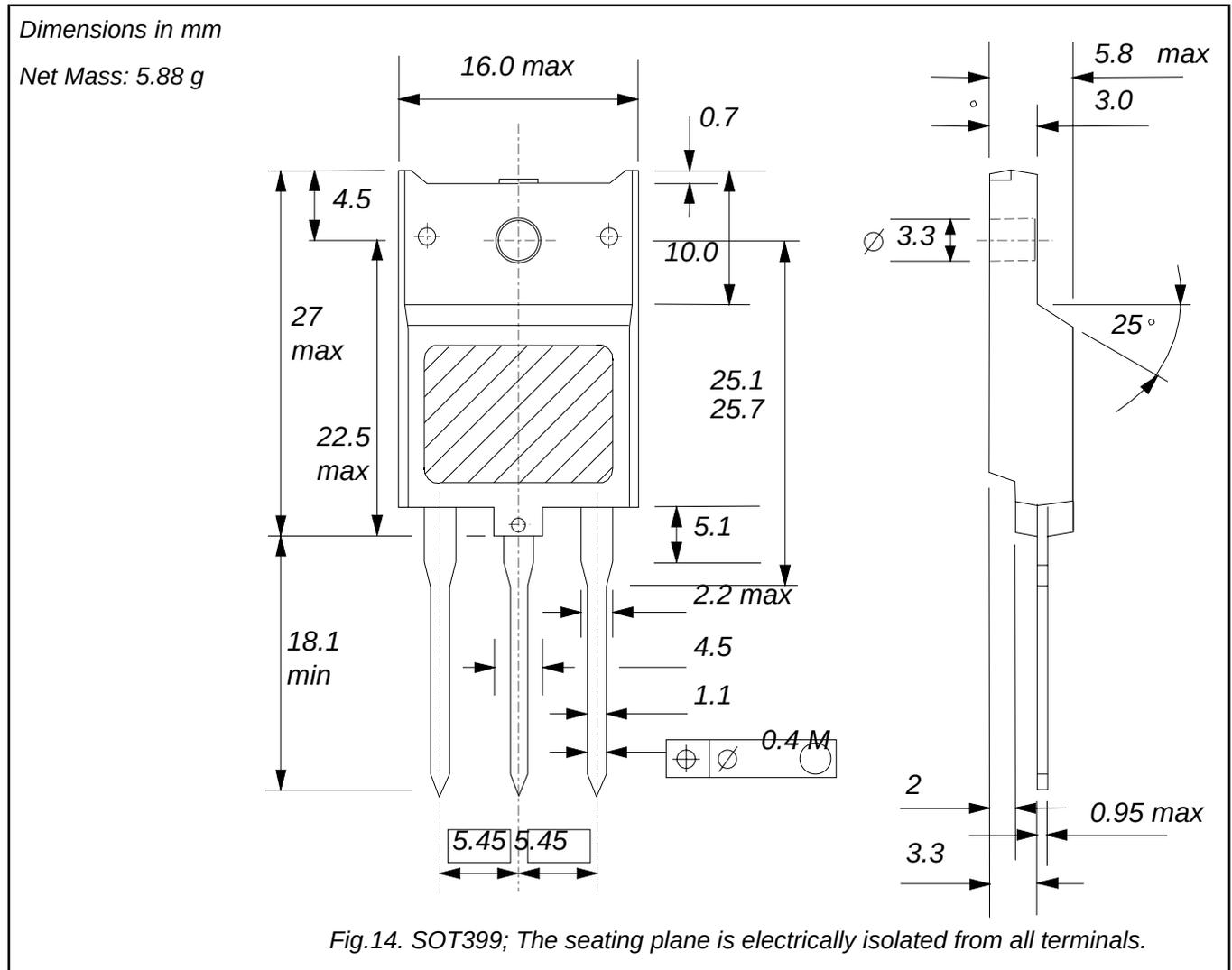


Fig.13. Forward bias safe operating area. $T_{hs} = 25^\circ C$
 I_{CDC} & $I_{CM} = f(V_{CE})$; I_{CM} single pulse; parameter t_p
Second-breakdown limits independent of temperature.
Mounted with heatsink compound.

MECHANICAL DATA



Notes

- 1. Refer to mounting instructions for F-pack envelopes.
- 2. Epoxy meets UL94 V0 at 1/8".

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DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	
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